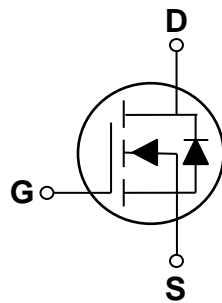
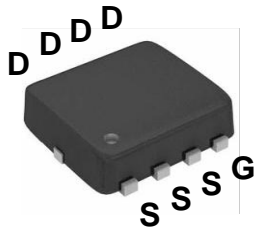


General Description

These N-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.

PPAK3X3 Pin Configuration



BVDSS	RDSON	ID
65V	17.5mΩ	32A

Features

- 65V,32A, $R_{DS(ON)} = 17.5m\Omega$ @ $V_{GS} = 10V$
- Improved dv/dt capability
- Fast switching
- 100% EAS Guaranteed
- Green Device Available

Applications

- Motor Drive
- Power Tools
- LED Lighting
- Quick Charger



Absolute Maximum Ratings $T_c=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	65	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Drain Current – Continuous ($T_c=25^\circ\text{C}$)	32	A
	Drain Current – Continuous ($T_c=100^\circ\text{C}$)	20.2	A
I_{DM}	Drain Current – Pulsed ¹	128	A
EAS	Single Pulse Avalanche Energy ²	45	mJ
IAS	Single Pulse Avalanche Current ²	30	A
P_D	Power Dissipation ($T_c=25^\circ\text{C}$)	46	W
	Power Dissipation – Derate above 25°C	0.37	W/ $^\circ\text{C}$
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction to ambient	---	62	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance Junction to Case	---	2.7	$^\circ\text{C/W}$

Electrical Characteristics (T_J=25 °C, unless otherwise noted)
Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	65	---	---	V
I _{DSS}	Drain-Source Leakage Current	V _{DS} =65V, V _{GS} =0V, T _J =25°C	---	---	1	μA
		V _{DS} =52V, V _{GS} =0V, T _J =125°C	---	---	10	μA
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA

On Characteristics

R _{DS(ON)}	Static Drain-Source On-Resistance ³	V _{GS} =10V, I _D =10A	---	14.5	17.5	mΩ
		V _{GS} =4.5V, I _D =5A	---	17.5	23	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250μA	1	1.7	2.5	V
g _{fs}	Forward Transconductance	V _{DS} =10V, I _D =3A	---	10	---	S

Dynamic and switching Characteristics

Q _g	Total Gate Charge ^{3,4}	V _{DS} =30V, V _{GS} =10V, I _D =10A	---	19.5	40	nC
Q _{gs}	Gate-Source Charge ^{3,4}		---	3.3	7	
Q _{gd}	Gate-Drain Charge ^{3,4}		---	2.3	5	
T _{d(on)}	Turn-On Delay Time ^{3,4}	V _{DD} =15V, V _{GS} =10V, R _G =6Ω I _D =1A	---	8.6	16	ns
T _r	Rise Time ^{3,4}		---	24.2	48	
T _{d(off)}	Turn-Off Delay Time ^{3,4}		---	32.3	64	
T _f	Fall Time ^{3,4}		---	7.9	16	
C _{iss}	Input Capacitance	V _{DS} =25V, V _{GS} =0V, F=1MHz	---	1310	2600	pF
C _{oss}	Output Capacitance		---	110	220	
C _{rss}	Reverse Transfer Capacitance		---	70	140	
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, F=1MHz	---	1.9	3.8	Ω

Drain-Source Diode Characteristics and Maximum Ratings

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current	V _G =V _D =0V, Force Current	---	---	32	A
I _{SM}	Pulsed Source Current ³		---	---	64	A
V _{SD}	Diode Forward Voltage ³	V _{GS} =0V, I _S =1A, T _J =25°C	---	---	1	V
t _{rr}	Reverse Recovery Time	V _{GS} =0V, I _S =1A, di/dt=100A/μs	---	19	---	ns
Q _{rr}	Reverse Recovery Charge	T _J =25°C	---	5	---	nC

Note :

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. V_{DD}=25V, V_{GS}=10V, L=0.1mH, I_{AS}=30A., R_G=25Ω, Starting T_J=25°C.
3. The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%.
4. Essentially independent of operating temperature.

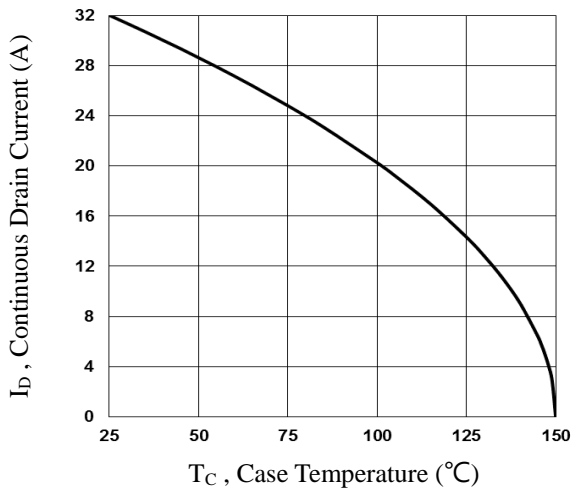


Fig.1 Continuous Drain Current vs. T_c

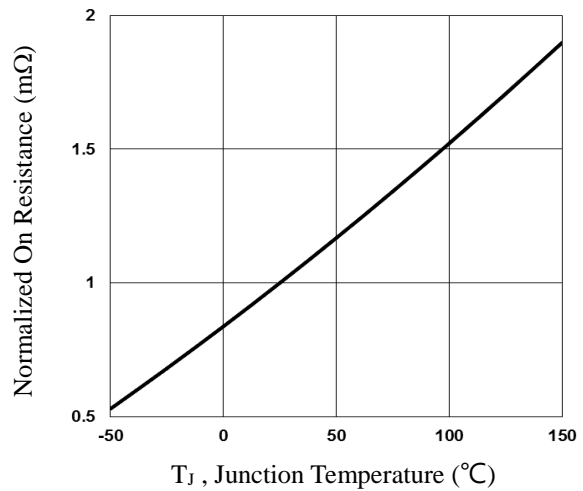


Fig.2 Normalized $R_{DS(on)}$ vs. T_j

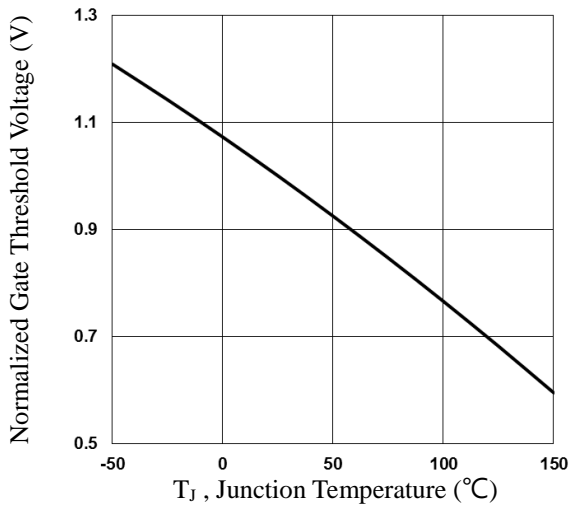


Fig.3 Normalized V_{th} vs. T_j

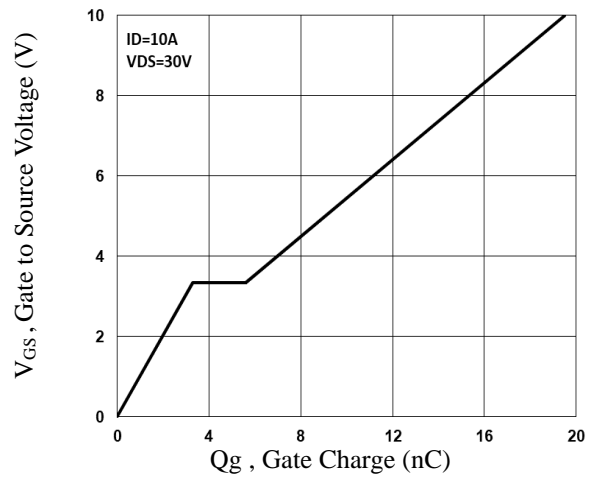


Fig.4 Gate Charge Waveform

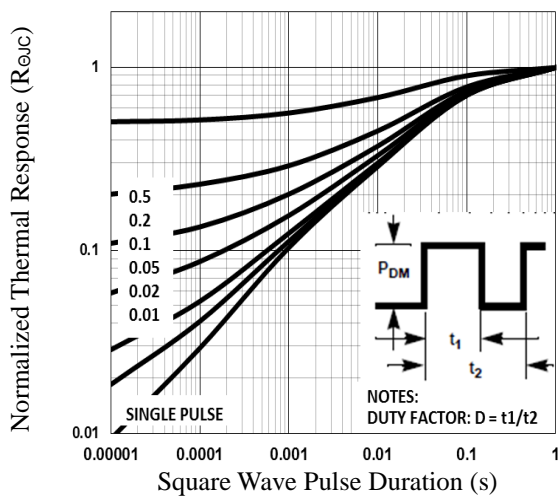


Fig.5 Normalized Transient Response

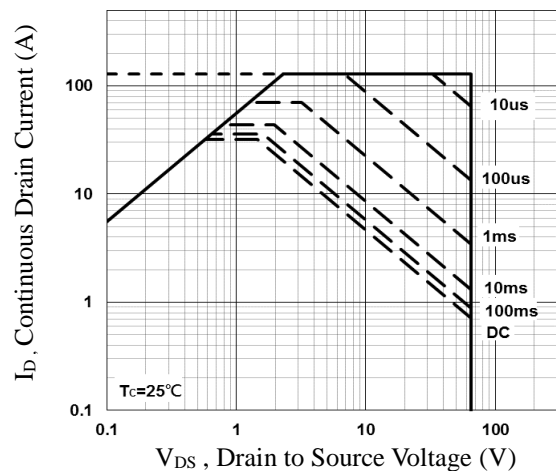


Fig.6 Maximum Safe Operation Area

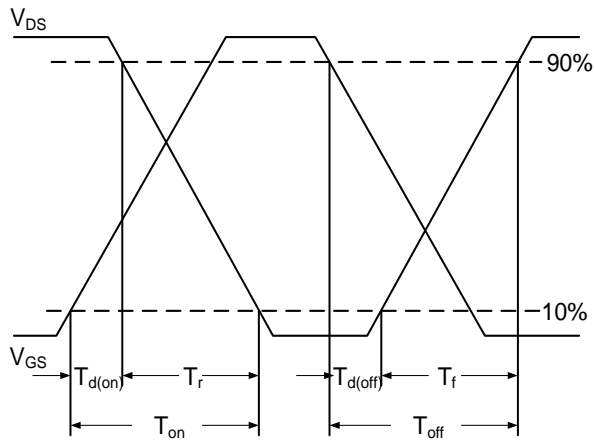


Fig.7 Switching Time Waveform

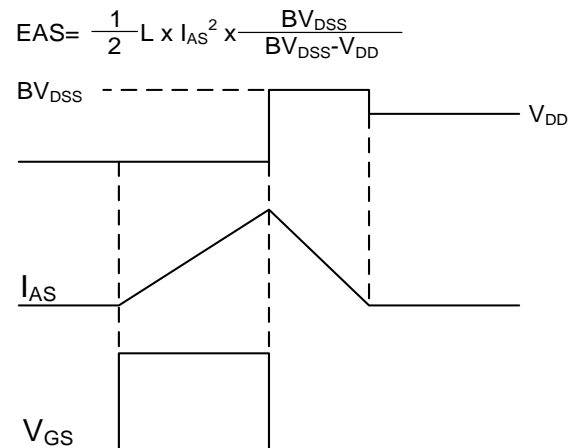
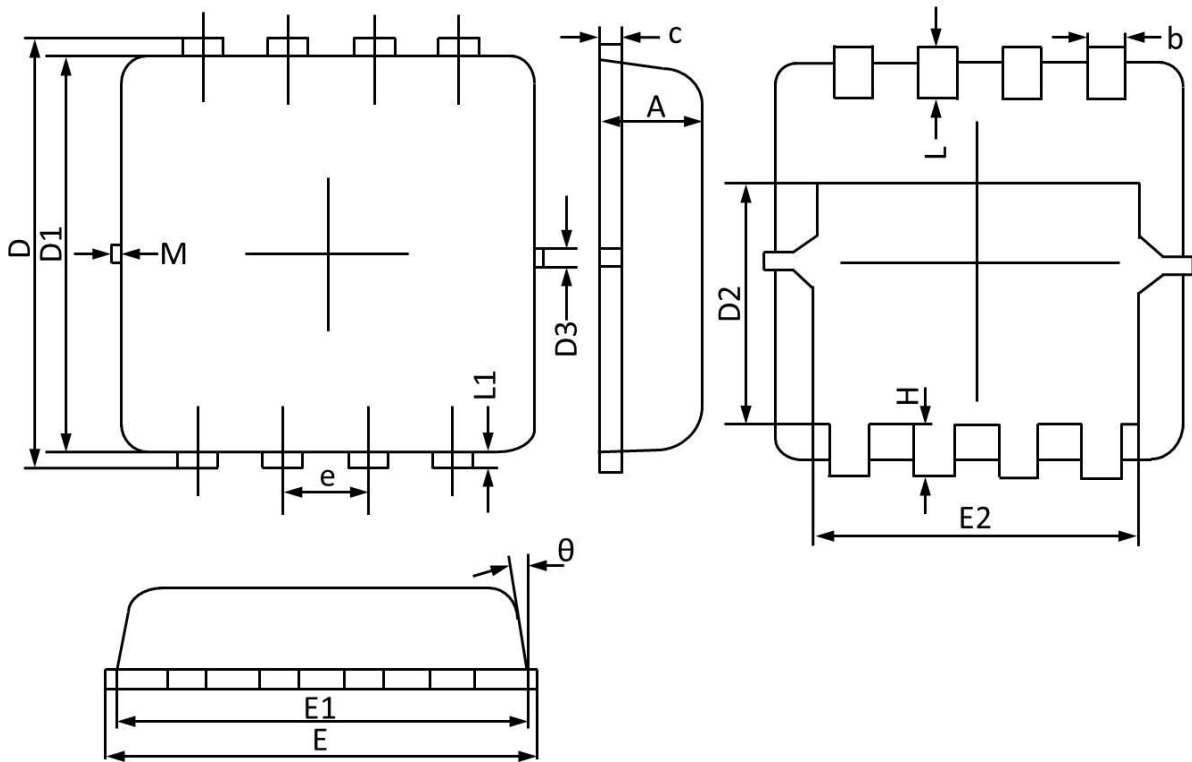


Fig.8 EAS Waveform

PPAK3x3 PACKAGE INFORMATION



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.700	0.800	0.028	0.031
b	0.250	0.350	0.010	0.013
c	0.100	0.250	0.004	0.009
D	3.250	3.450	0.128	0.135
D1	3.000	3.200	0.119	0.125
D2	1.780	1.980	0.070	0.077
D3	0.130 REF		0.005 REF	
E	3.200	3.400	0.126	0.133
E1	3.000	3.200	0.119	0.125
E2	2.390	2.590	0.094	0.102
e	0.650 BSC		0.026 BSC	
H	0.300	0.500	0.011	0.019
L	0.300	0.500	0.011	0.019
L1	0.130 REF		0.005 REF	
θ	0°	12°	0°	12°
M	0.150 REF		0.006 REF	